

Automotive N-Channel 100 V (D-S) 175 °C MOSFET

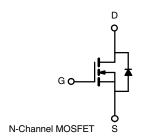
PRODUCT SUMMARY				
V _{DS} (V)	100			
$R_{DS(on)}$ (Ω) at V_{GS} = 10 V	0.0095			
I _D (A)	120			
Configuration	Single			
Package	TO-220			

FEATURES

- TrenchFET® power MOSFET
- Package with low thermal resistance
- AEC-Q101 qualified d
- 100 % R_a and UIS tested
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>







ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)					
PARAMETER	SYMBOL	LIMIT	UNIT		
Drain-Source Voltage		V _{DS}	100	V	
Gate-Source Voltage		V_{GS}	± 20	V	
Continuous Drain Current	T _C = 25 °C ^a	I _D	120		
Continuous Diain Current	T _C = 125 °C		73		
Continuous Source Current (Diode Conduction	I _S	120	Α		
Pulsed Drain Current ^b	I _{DM}	480			
Single Pulse Avalanche Current	L = 0.1 mH	I _{AS}	73		
Single Pulse Avalanche Energy	L = 0.1 IIII	E _{AS}	266	mJ	
Maximum Power Dissipation ^b	T _C = 25 °C	P _D	375	W	
iviaximum i owei bissipation -	T _C = 125 °C		125	VV	
Operating Junction and Storage Temperature	T _J , T _{stg}	-55 to +175	°C		

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	LIMIT	UNIT	
Junction-to-Ambient	PCB Mount c	R _{thJA}	40	°C/W	
Junction-to-Case (Drain)		R _{thJC}	0.4	G/VV	

Notes

- a. Package limited.
- b. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.
- c. When mounted on 1" square PCB (FR4 material).
- d. Parametric verification ongoing.



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PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT	
Static					l			
Drain-Source Breakdown Voltage	V _{DS}	V _{GS}	= 0, I _D = 250 μA	100	-	-	V	
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} =	= V _{GS} , I _D = 250 μA	2.5	3.0	3.5	V	
Gate-Source Leakage	I _{GSS}	V _{DS} =	0 V, V _{GS} = ± 20 V	-	-	± 100	nA	
		V _{GS} = 0 V	V _{DS} = 100 V	-	-	1		
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V	V _{DS} = 100 V, T _J = 125 °C	-	-	50	μΑ	
		V _{GS} = 0 V	V _{DS} = 100 V, T _J = 175 °C	-	-	150		
On-State Drain Current ^a	I _{D(on)}	V _{GS} = 10 V	$V_{DS} \ge 5 \text{ V}$	120	-	-	Α	
		V _{GS} = 10 V	I _D = 30 A	-	0.0079	0.0095		
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 10 V	I _D = 30 A, T _J = 125 °C	-	-	0.0190	Ω	
		V _{GS} = 10 V	I _D = 30 A, T _J = 175 °C	-	-	0.0250		
Forward Transconductance b	9 _{fs}	V _{DS}	= 15 V, I _D = 30 A	-	99	-	S	
Dynamic ^b					•			
Input Capacitance	C _{iss}			-	6915	8645		
Output Capacitance	C _{oss}	V _{GS} = 0 V	V _{DS} = 25 V, f = 1 MHz	-	635	795	pF	
Reverse Transfer Capacitance	C _{rss}			-	280	350		
Total Gate Charge ^c	Qg			-	120	180		
Gate-Source Charge ^c	Q _{gs}	V _{GS} = 10 V	$V_{DS} = 50 \text{ V}, I_D = 85 \text{ A}$	-	30	-	nC	
Gate-Drain Charge ^c	Q _{gd}			-	28.5	-		
Gate Resistance	R _g		f = 1 MHz	0.25	0.7	2.3	Ω	
Turn-On Delay Time ^c	t _{d(on)}		$V_{DD} = 50 \text{ V}, \text{ R}_{L} = 0.6 \Omega$		21	32		
Rise Time ^c	t _r	V _{DD} :			24	36	ns	
Turn-Off Delay Time ^c	t _{d(off)}	$I_D \cong 85 \text{ Å}, V_{GEN} = 10 \text{ V}, R_g = 2.5 \Omega$		-	52	78		
Fall Time ^c	t _f			-	16	24		
Source-Drain Diode Ratings and Chara	acteristics b				•			
Pulsed Current ^a	I _{SM}			-	-	480	Α	
Forward Voltage	V _{SD}	I _F	I _F = 85 A, V _{GS} = 0		0.9	1.5	V	

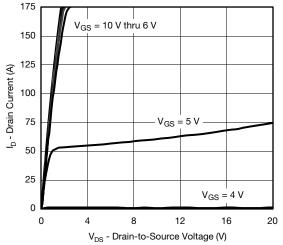
Notes

- a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

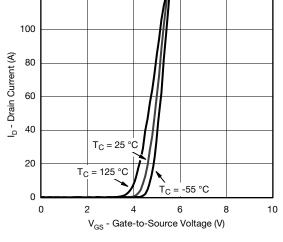
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



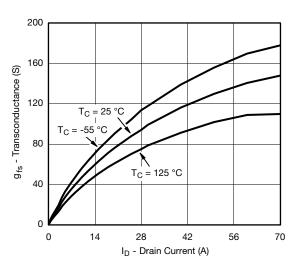
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



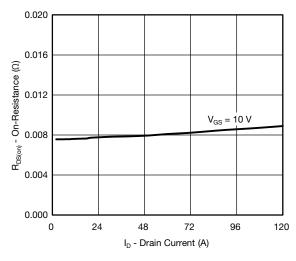
Output Characteristics



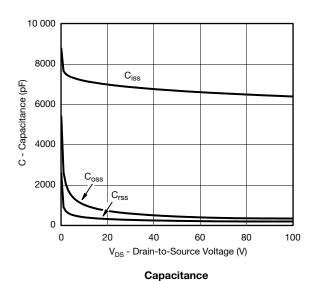
Transfer Characteristics

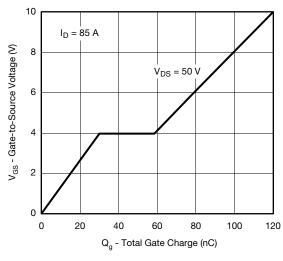


Transconductance



On-Resistance vs. Drain Current

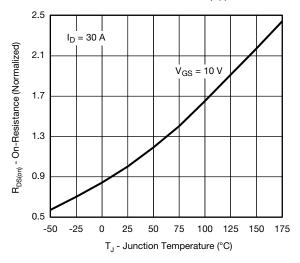




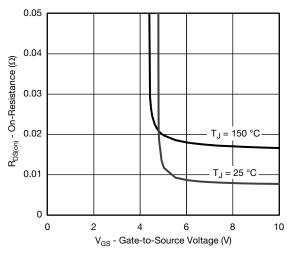
Gate Charge



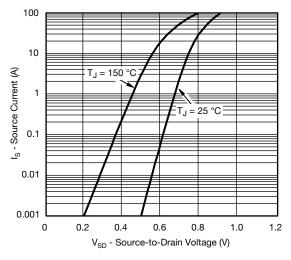
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



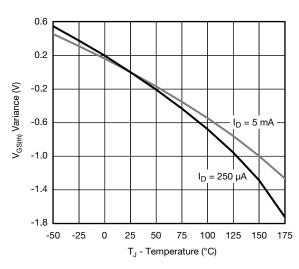
On-Resistance vs. Junction Temperature



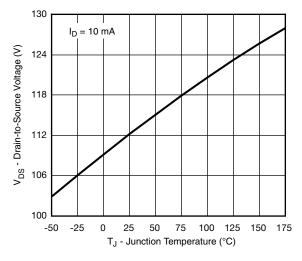
On-Resistance vs. Gate-to-Source Voltage



Source Drain Diode Forward Voltage



Threshold Voltage

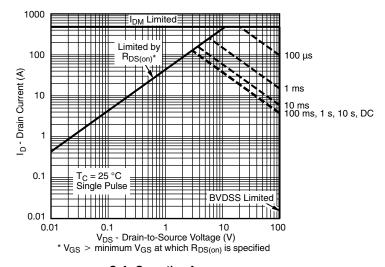


Drain Source Breakdown vs. Junction Temperature

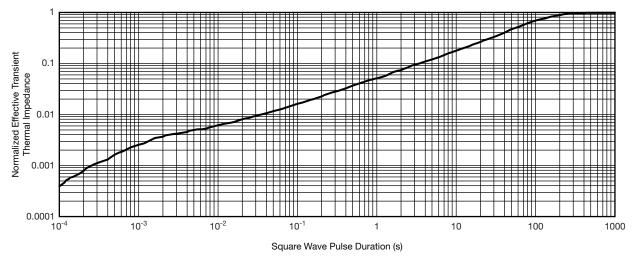
For technical questions, contact: automostech



THERMAL RATINGS ($T_A = 25$ °C, unless otherwise noted)

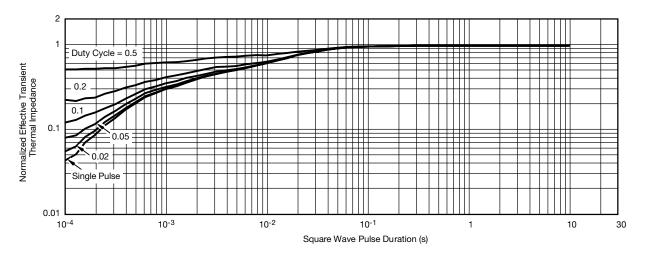


Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient

THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction to Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction to Case (25 °C) are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

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REVISION HISTORY ^a				
REVISION	DATE	DESCRIPTION OF CHANGE		
В	04-Aug-15	Revised R _g minimum limit		

Note

a. As of April 2014



TO-220

Ordering codes for the SQ rugged series power MOSFETs in the TO-220 package:

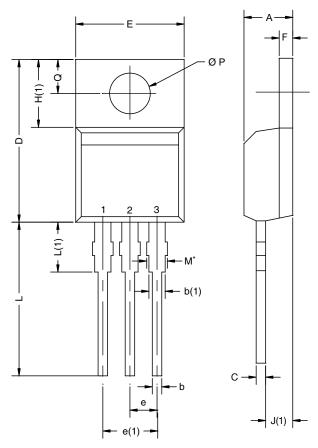
DATASHEET PART NUMBER	OLD ORDERING CODE ^a	NEW ORDERING CODE
SQP100N04-3m6	-	SQP100N04-3M6_GE3
SQP100P06-9m3L	-	SQP100P06-9M3L_GE3
SQP120N06-06	-	SQP120N06-06_GE3
SQP120N06-3m5L	SQP120N06-3M5L-GE3	SQP120N06-3M5L_GE3
SQP120N10-09	SQP120N10-09-GE3	SQP120N10-09_GE3
SQP120N10-3m8	SQP120N10-3M8-GE3	SQP120N10-3M8_GE3
SQP25N15-52	-	SQP25N15-52_GE3
SQP50N06-09L	SQP50N06-09L-GE3	SQP50N06-09L_GE3
SQP50P03-07	SQP50P03-07-GE3	SQP50P03-07_GE3
SQP60N06-15	SQP60N06-15-GE3	SQP60N06-15_GE3
SQP90P06-07L	SQP90P06-07L-GE3	SQP90P06-07L_GE3

Note

a. Old ordering code is obsolete and no longer valid for new orders



TO-220AB



		D2

	MILLIN	IETERS	INC	HES	
DIM.	MIN.	MAX.	MIN.	MAX.	
А	4.25	4.65	0.167	0.183	
b	0.69	1.01	0.027	0.040	
b(1)	1.20	1.73	0.047	0.068	
С	0.36	0.61	0.014	0.024	
D	14.85	15.49	0.585	0.610	
D2	12.19	12.70	0.480	0.500	
Е	10.04	10.51	0.395	0.414	
е	2.41	2.67	0.095	0.105	
e(1)	4.88	5.28	0.192	0.208	
F	1.14	1.40	0.045	0.055	
H(1)	6.09	6.48	0.240	0.255	
J(1)	2.41	2.92	0.095	0.115	
L	13.35	14.02	0.526	0.552	
L(1)	3.32	3.82	0.131	0.150	
ØΡ	3.54	3.94	0.139	0.155	
Q	2.60	3.00	0.102	0.118	
ECN: T14-0413-Rev. P, 16-Jun-14 DWG: 5471					

Note

 * M = 1.32 mm to 1.62 mm (dimension including protrusion) Heatsink hole for HVM



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Revision: 02-Oct-12 Document Number: 91000

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IPS70R2K0CEAKMA1 BUK954R8-60E DMN3404LQ-7 NTE6400 SQJ402EP-T1-GE3 2SK2614(TE16L1,Q) 2N7002KW-FAI

DMN1017UCP3-7 EFC2J004NUZTDG ECH8691-TL-W FCAB21350L1 P85W28HP2F-7071 DMN1053UCP4-7 NTE221 NTE2384

NTE2903 NTE2941 NTE2945 NTE2946 NTE2960 NTE2967 NTE2969 NTE2976 NTE455 NTE6400A NTE2910 NTE2916 NTE2956

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